L Number	Hits	Search Text	DB	Time stamp
-	1	("20040124460").PN.	USPAT;	2004/07/08 10:28
		, ,	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1130	(438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT;	2004/07/08 13:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2141	(nitriding nitridation) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 13:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	147	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:42
		((nitriding nitridation) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	832	(nitriding nitridation) with (poly polysilicon gate near	USPAT;	2004/07/08 10:39
		electrode)	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	53	(((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 10:39
		((nitriding nitridation) with (poly polysilicon gate electrode)))	US-PGPUB;	_ ,, ,
		and ((nitriding nitridation) with (poly polysilicon gate near	EPO; JPO;	
		electrode))	DERWENT;	
		**************************************	IBM_TDB	
-	264	(rtn) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:44
		, , , , , , ,	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:45
		((rtn) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	679	(m) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:45
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:45
]	-	((rn) with (poly polysilicon gate electrode))	US-PGPUB;	
			EPO; JPO;	
ļ l			DERWENT;	
			IBM_TDB	
-	80	(rpn) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 11:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
] -	11	((438/148,768,769,775,776,791,792,793,794).CCLS.) and	USPAT;	2004/07/08 11:47
		((rpn) with (poly polysilicon gate electrode))	US-PGPUB;	
j			EPO; JPO;	
			DERWENT;	
			_IBM_TDB	

-	1810	(oxidation oxide oxidize) near2 side near2 (gate electrode)	USPAT; US-PGPUB; EPO; JPO;	2004/07/08 11:48
			DERWENT;	
_	2841	(nitriding nitridation rtp rtn) with (poly polysilicon gate	IBM_TDB USPAT;	2004/07/10 09:48
		electrode)	US-PGPUB;	200 1/07/10 05: 10
			EPO; JPO;	
			DERWENT; IBM_TDB	
_	63	((oxidation oxide oxidize) near2 side near2 (gate electrode))	USPAT;	2004/07/08 11:48
		and ((nitriding nitridation rtp rtn) with (poly polysilicon gate	US-PGPUB;	
		electrode))	EPO; JPO; DERWENT;	
			IBM_TDB	
-	57	(nitriding nitridation) with (poly polysilicon gate electrode)	USPAT;	2004/07/08 13:35
		and (metal titanium tungsten molybdium nickel cobalt) near	US-PGPUB;	
		nitride same (nitrided silicion near nitride)	EPO; JPO; DERWENT;	
			IBM_TDB	
-	21	("5147820" "5256455" "5279985" "5352623"	USPAT	2004/07/08 13:29
		"5438012" "5486488" "5508221" "5619051" "5696017" "5763315" "5801079" "5805494"		
		"5807760" "5811336" "5854114" "5856009"		
		"5858873" "6146959" "6171970" "6277681"		
_	4436	"6319856").PN. ((nitriding nitridation) with (thermal decoupled near plasma	USPAT;	2004/07/08 13:40
	1150	remote near plasma) dpn rpn cvd chemical near vapor near	US-PGPUB;	200 1/0//00 10:10
		deposition ald atomic near layer near deposition) with (poly	EPO; JPO;	,
		polysilicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4")	DERWENT; IBM_TDB	
_	12068	((nitriding nitridation) with (thermal decoupled near plasma	USPAT;	2004/07/08 13:41
		remote near plasma) dpn rpn cvd chemical near vapor near	US-PGPUB;	
		deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride	EPO; JPO; DERWENT;	
		sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si	IBM_TDB	
		polysilicon silicon) with (gate electrode)		2004/07/20 12 13
-	9288	(pattern patterning etch\$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si)	USPAT; US-PGPUB;	2004/07/08 13:43
		(manaci manaci manacion) man (sincom pory porysincom si)	EPO; JPO;	
			DERWENT;	
_	3068	(pattern patterning etch\$5) with (gate electrode) with	IBM_TDB USPAT;	2004/07/08 13:45
	3000	(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	200 1/07/00 13.43
		and (((nitriding nitridation) with (thermal decoupled near	EPO; JPO;	
		plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition)	DERWENT; IBM_TDB	
		with (poly si polysilicon silicon gate electrode) with (silicon	100-100	
		near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and		
_	1130	(poly si polysilicon silicon) with (gate electrode)) (438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT;	2004/07/08 13:43
	1130	(130) 130,100,103,113,110,131,132,133,137).CCL3.	US-PGPUB;	2007/07/00 13:43
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	

-	63	((pattern patterning etch\$5) with (gate electrode) with	USPAT; US-PGPUB;	2004/07/08 13:46
•		(nitride nitrided nitridation) with (silicon poly polysilicon si) and (((nitriding nitridation) with (thermal decoupled near	EPO; JPO;	
		plasma remote near plasma) dpn rpn cvd chemical near	DERWENT;	
		vapor near deposition ald atomic near layer near deposition)	IBM_TDB	
			םטו_ושם	
		with (poly si polysilicon silicon gate electrode) with (silicon		
		near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and		
,		(poly si polysilicon silicon) with (gate electrode))) and		
	665	((438/148,768,769,775,776,791,792,793,794).CCLS.)	LICDAT.	2004/07/00 12:46
-	665	(pattern patterning etch\$5) with (gate electrode) with	USPAT;	2004/07/08 13:46
		(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	
		with (metal titanium tungsten molybdium nickel cobalt Ti W Mo Ni Co) and (((nitriding nitridation) with (thermal	EPO; JPO; DERWENT;	
		decoupled near plasma remote near plasma) dpn rpn cvd	IBM_TDB	
		chemical near vapor near deposition ald atomic near layer	םם ו_ויוםנ	
		near deposition) with (poly si polysilicon silicon gate		
		electrode) with (silicon near nitride sin "si.sub.3n.sub.4"		
		"si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate		
_	17	electrode)) ((pattern patterning etch\$5) with (gate electrode) with	USPAT;	2004/07/08 15:36
-	1/	(nitride nitrided nitridation) with (silicon poly polysilicon si)	US-PGPUB;	2007/07/00 13.30
		with (metal titanium tungsten molybdium nickel cobalt Ti W	EPO; JPO;	
		Mo Ni Co) and (((nitriding nitridation) with (thermal	DERWENT;	
		decoupled near plasma remote near plasma) dpn rpn cvd	IBM_TDB	
		chemical near vapor near deposition ald atomic near layer	10/1_100	
		near deposition) with (poly si polysilicon silicon gate		
		electrode) with (silicon near nitride sin "si.sub.3n.sub.4"		
		"si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate		
		electrode))) and		
		((438/148,768,769,775,776,791,792,793,794).CCLS.)		
-	25	surface near density near (nitrogen "n.sub.2")	USPAT;	2004/07/08 17:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	("5719410").PN.	USPAT;	2004/07/08 16:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2004/07/00 47 07
-	2	jp-60195975-\$.did.	USPAT;	2004/07/08 17:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
<u> </u>	990340	ITO, TAKASHI	USPAT;	2004/07/08 17:26
-	7703 4 0	HORIE, HIROSHI	US-PGPUB;	2007/07/00 17:20
		SUGII, TOSHIHIRO	EPO; JPO;	
		Journ 103Hillino	DERWENT;	
			IBM_TDB	<u> </u>
_	990340	ITO, TAKASHI	USPAT;	2004/07/08 17:26
	7,703,70	HORIE, HIROSHI	US-PGPUB;	230 1/07/00 17.20
		SUGII, TOSHIHIRO TAKASHI-ITO	EPO; JPO;	
		The state of the s	DERWENT;	
			IBM_TDB	
-	3132	SUGII-TOSHIHIRO TAKASHI-ITO HORIE-HIROSHI	USPAT;	2004/07/08 17:28
_		ito-takashi TOSHIHIRO-SUGII	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	·			<u> </u>

-	241	(438/\$6 257/\$6) and (SUGII-TOSHIHIRO TAKASHI-ITO	USPAT;	2004/07/10 09:47
		HORIE-HIROSHI ito-takashi TOSHIHIRO-SUGII)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	33	4935804.URPN.	USPAT	2004/07/08 17:46
-	6	("3755026" "4117506" "4141022" "4377857"	USPAT	2004/07/08 17:46
		"4460980" "4558344").PN.		
_	73	(decoupled near plasma near nitridation remote near plasma	USPAT;	2004/07/10 09:48
		near nitridation) with (poly polysilicon gate electrode)	US-PGPUB;	
		The first addition The first Polyonicon gate close cae	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
l _	0	(decoupled near plasma near nitridation remote near plasma	USPAT;	2004/07/10 09:49
-	"			2004/07/10 05.45
		near nitridation) with (poly polysilicon gate electrode) with	US-PGPUB;	
		(ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(decoupled near plasma near nitridation remote near plasma	USPAT;	2004/07/10 09:53
		near nitridation) with (poly polysilicon gate electrode) same	US-PGPUB;	
		(ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
-			DERWENT;	
			IBM_TDB	
-	6	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 09:56
		plasma near nitridation rpn) with (poly polysilicon gate	US-PGPUB;	
		electrode) same (ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
		, ,	DERWENT;	
	[IBM_TDB	
-	1 4	((decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 09:53
		plasma near nitridation rpn) with (poly polysilicon gate	US-PGPUB;	
		electrode) same (ammonia "nh.sub.3" "n h.sub.3")) not	EPO; JPO;	
	ŀ	((decoupled near plasma near nitridation remote near	DERWENT;	
		plasma near nitridation) with (poly polysilicon gate	IBM_TDB	
		electrode) same (ammonia "nh.sub.3" "n h.sub.3"))	1011_100	
_	8	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:16
		plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	2001/07/10 10:10
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") not	EPO; JPO;	
		((decoupled near plasma near nitridation dpn remote near	DERWENT;	
			· '	
		plasma near nitridation rpn) with (poly polysilicon gate	IBM_TDB	
	_	electrode) same (ammonia "nh.sub.3" "n h.sub.3"))	LICDAT.	2004/07/10 10:15
-	0	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:16
		plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") with	EPO; JPO;	
		("1000") near (w watt watts)	DERWENT;	
			IBM_TDB	2004/07/40 40 54
-	1	(decoupled near plasma near nitridation dpn remote near	USPAT;	2004/07/10 10:34
		plasma near nitridation rpn) with (poly polysilicon silicon si	US-PGPUB;	
		gate electrode) same (ammonia "nh.sub.3" "n h.sub.3")	EPO; JPO;	
		same ("1000") near (w watt watts)	DERWENT;	
			IBM_TDB	
-	0	jp-200049159-\$.did.	USPAT;	2004/07/10 10:34
			US-PGPUB;	
}	,		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-2000049159-\$.did.	USPAT;	2004/07/10 10:34
		<u>'</u>	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
				<u> </u>